

ABSTRACT

Disclosed are a semiconductor memory device and a method of manufacturing the same. The semiconductor memory device comprises a cell array region and a peripheral circuit region. The cell array region comprises a plurality of electrode structures including a plurality of electrodes that sequentially stacked on a body conductive layer, and a plurality of vertical structures that penetrate the electrode structures and are connected to the body conductive layer. The peripheral circuit region comprises a residual substrate and a peripheral transistor on the residual substrate. The residual substrate has a top surface higher than that of the body conductive layer.

FIG. 2B